



**Alfa-MOS
Technology**

AFE0524P
**Ultra Low Capacitance 4-Channel
ESD Protection Array**

General Description

The AFE0524P is a 4-channel ultra low capacitance rail clamp ESD protection diodes array. Each channel consists of a pair of ESD diodes that steer positive or negative ESD current to either the positive or negative rail.

A zener diode is integrated in to the array between the positive and negative supply rails. In the typical applications, the negative rail pin (assigned as GND) is connected with system ground. The Positive ESD current is steered to the ground through an ESD diode and Zener diode and the positive ESD voltage is clamped to the zener voltage.

The AFE0524P is idea to protect high speed data lines.

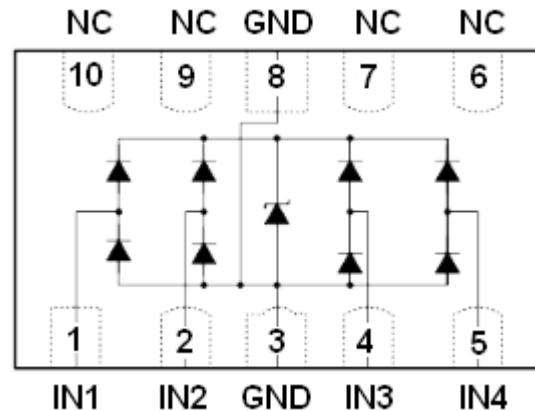
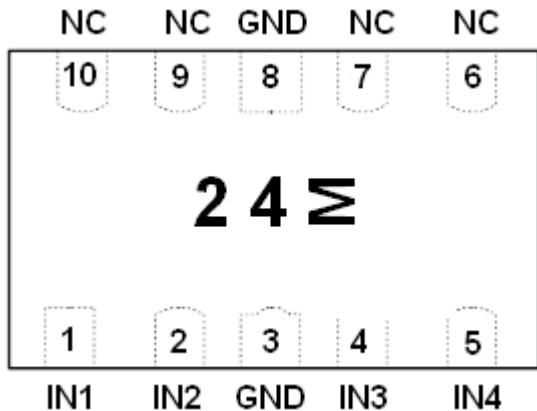
Features

- 4 channels of ESD protection
- Provides ESD protection to IEC61000-4-2 level 4
±15 KV air discharge
±8 KV contact discharge
- Channel I/O to GND capacitance: 0.6pF(Max)
- Channel I/O to I/O capacitance: 0.45pF(Max)
- Low clamping voltage
- 5V low operating voltage
- Improved Zener structure
- Optimized package for easy high speed data lines PCB layout
- ROHS compliant

Application

- High Definition Multi-Media Interface Protection
- USB 3.0 Power and Data Line Protection
- Monitors and Flat Panel Displays Notebook Computers
- Video Line Protection & Base Stations
- HDSL, IDSL Secondary IC Side Protection
- Microcontroller Input Protection
- LCD and camera modules
- 10/100/1000 Ethernet

Pin Description Top View (DFN-10)



Ordering Information

| Part Ordering No. | Part Marking | Package | Unit | Quantity |
|-------------------|--------------|---------|-------------|----------|
| AFE0524PFN10RG | 24M | DFN-10 | Tape & Reel | 3000 EA |

※ 24 Specific Device Code

※ M Month Code

※ AFE0524PFN10RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



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ABSOLUTE MAXIMUM RATINGS

($T_A=25^\circ\text{C}$ Unless otherwise noted)

| Parameter | Symbol | Typical | Unit |
|---|------------|-----------|------------------|
| Peak Pulse Power ($t_p = 8/20 \mu\text{s}$) | P_{pk} | 150 | W |
| Peak Pulse Current ($t_p = 8/20 \mu\text{s}$) | I_{PP} | 5 | A |
| ESD per IEC 61000 – 4 – 2 (Air) | V_{ESD1} | ± 15 | KV |
| ESD per IEC 61000 – 4 – 2 (Contact) | V_{ESD2} | ± 8 | KV |
| Operating Junction Temperature | T_J | -55 ~ 125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | -55 ~ 150 | $^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS

($T_A=25^\circ\text{C}$ Unless otherwise noted)

| Parameter | Symbol | Conditions | Min. | Typ | Max. | Unit |
|---|-----------|---|------|------|------|---------------|
| Reverse Working Voltage | V_{RWM} | Any Pin to GND | | | 5 | V |
| Forward Voltage | V_F | $I_F = 10\text{mA}$ | 0.4 | 0.8 | 1.5 | V |
| Reverse Breakdown Voltage | V_{BR} | $I_t = 1\text{mA}$ Any Pin to GND | 6 | | | V |
| Reverse Leakage Current | I_R | $V_{RWM} = 5\text{V}$, $T=25^\circ\text{C}$ Any Pin to GND | | 0.03 | 1 | μA |
| Positive Clamping Voltage | V_{C1} | $I_{PP} = 1\text{A}$, $t_p = 8/20 \mu\text{s}$ Positive pulse Any Pin to GND | | 8.5 | 12 | V |
| Negative Clamping Voltage | V_{C2} | $I_{PP} = 1\text{A}$, $t_p = 8/20 \mu\text{s}$ Negative pulse Any Pin to GND | | 1.8 | | V |
| Junction Capacitance Between Channel | C_{j1} | $V_R = 0\text{V}$, $f = 1\text{MHz}$ Between I/O Pin | | 0.35 | 0.45 | pF |
| Junction Capacitance Between I/O to GND | C_{j2} | $V_R = 0\text{V}$, $f = 1\text{MHz}$ Any Pin to GND | | 0.5 | 0.6 | pF |



Electrical Parameter

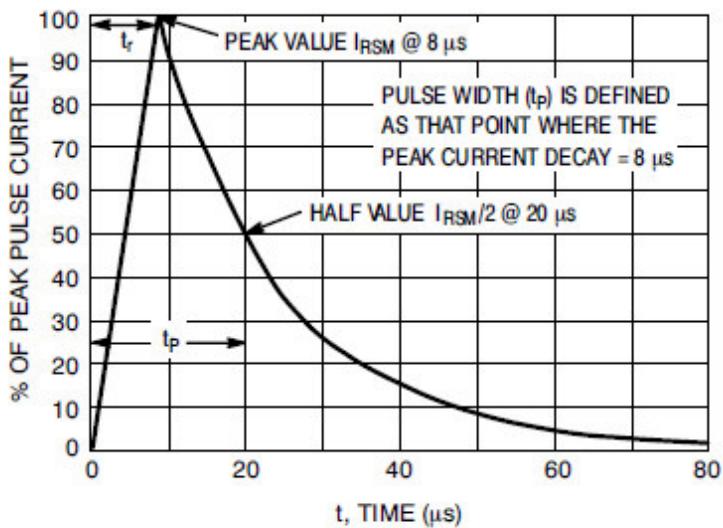
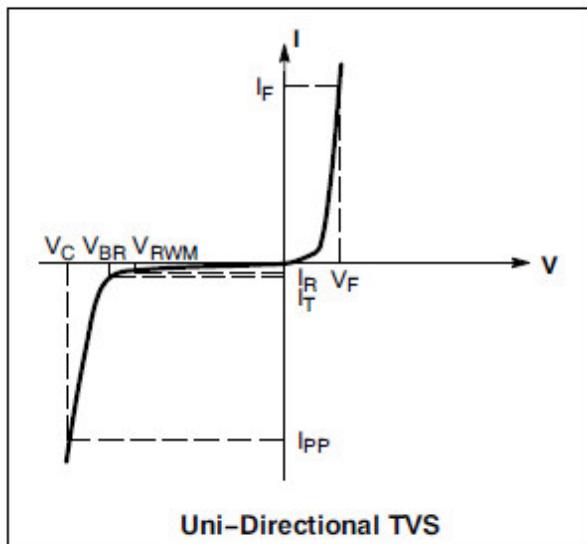


Figure 1. 8 X 20 μs Pulse Waveform

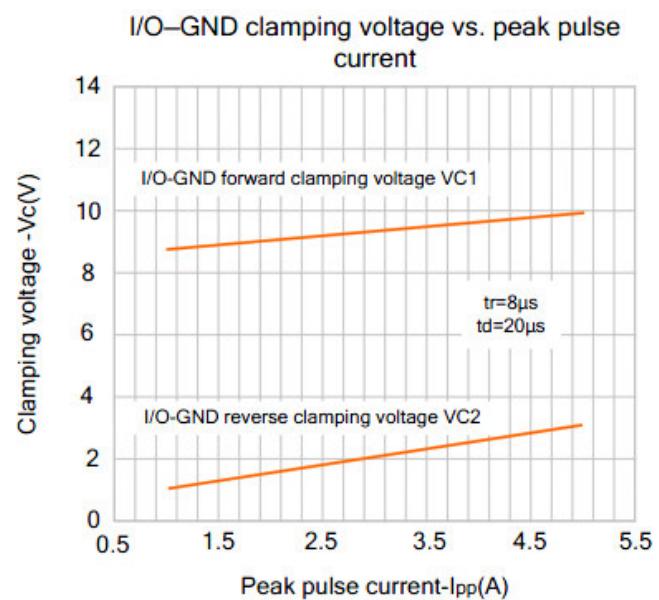
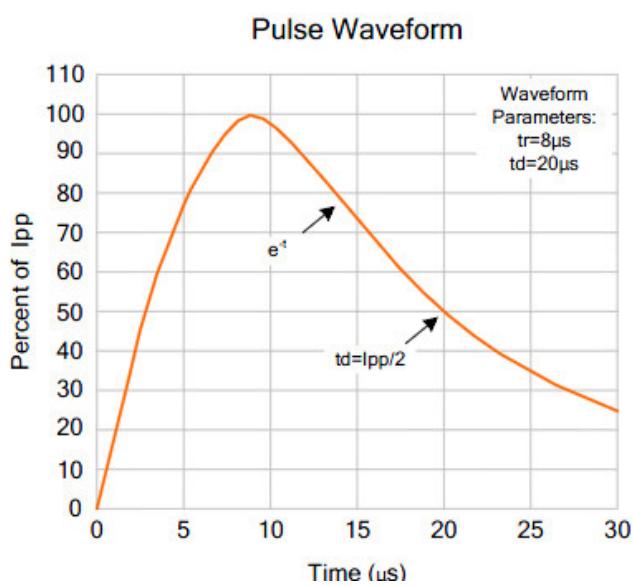
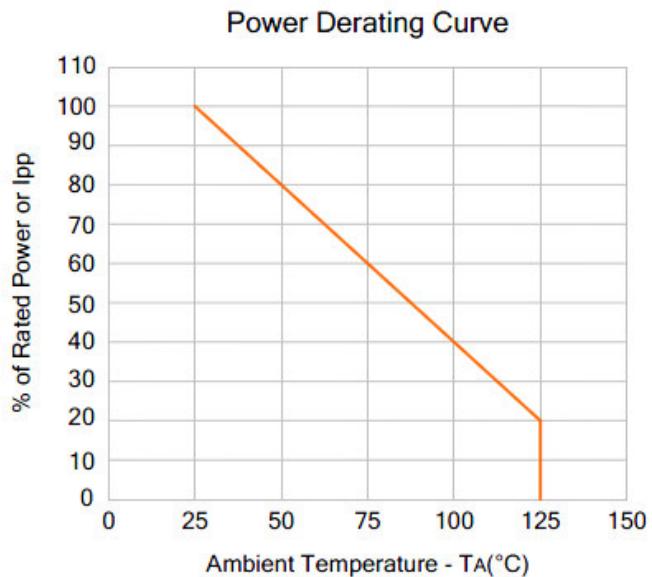
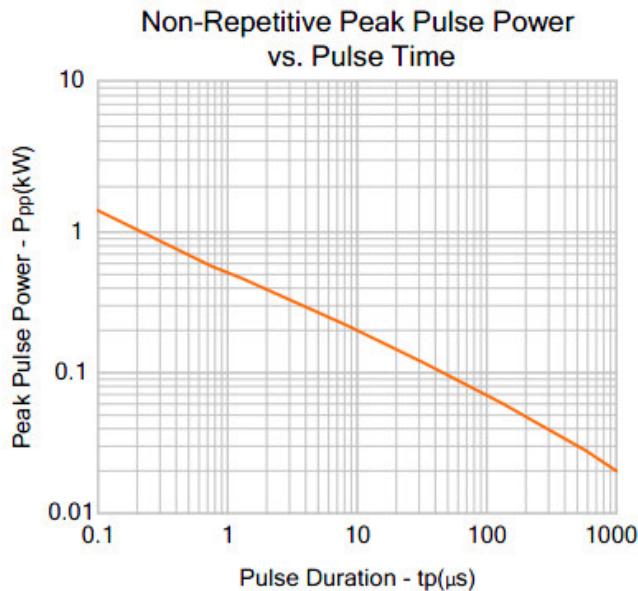
| Symbol | Parameter |
|-----------|--|
| I_{PP} | Maximum Reverse Peak Pulse Current |
| V_C | Clamping Voltage @ IPP |
| V_{RWM} | Working Peak Reverse Voltage |
| I_R | Maximum Reverse Leakage Current @ VRWM |
| I_T | Test Current |
| V_{BR} | Breakdown Voltage @ IT |
| I_F | Forward Current |
| V_F | Forward Voltage @ IF |



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Typical Characteristics

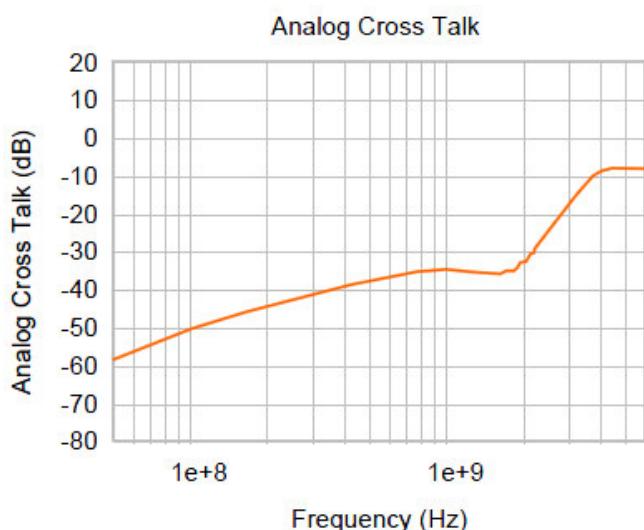
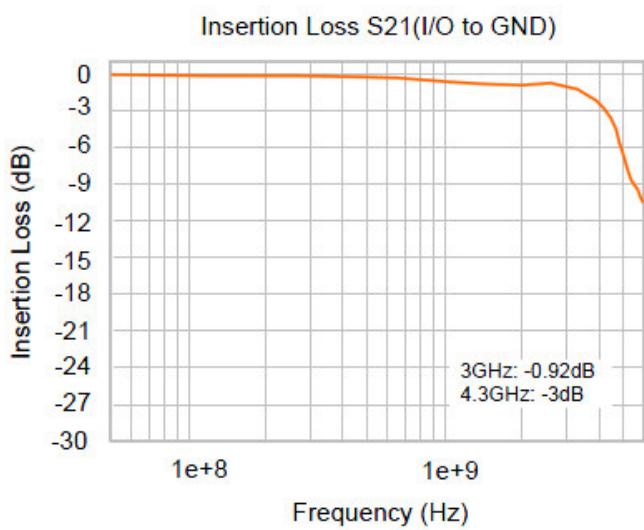
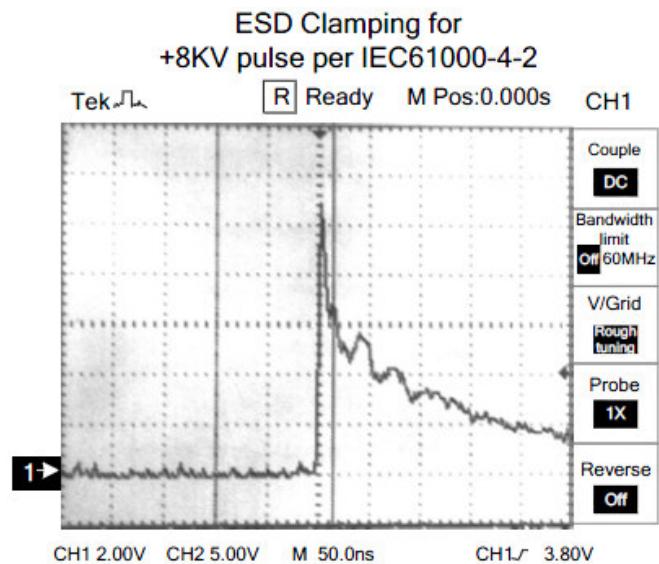
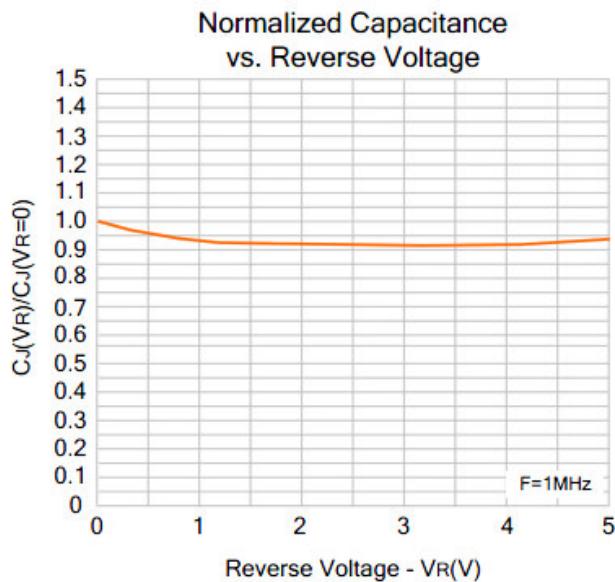




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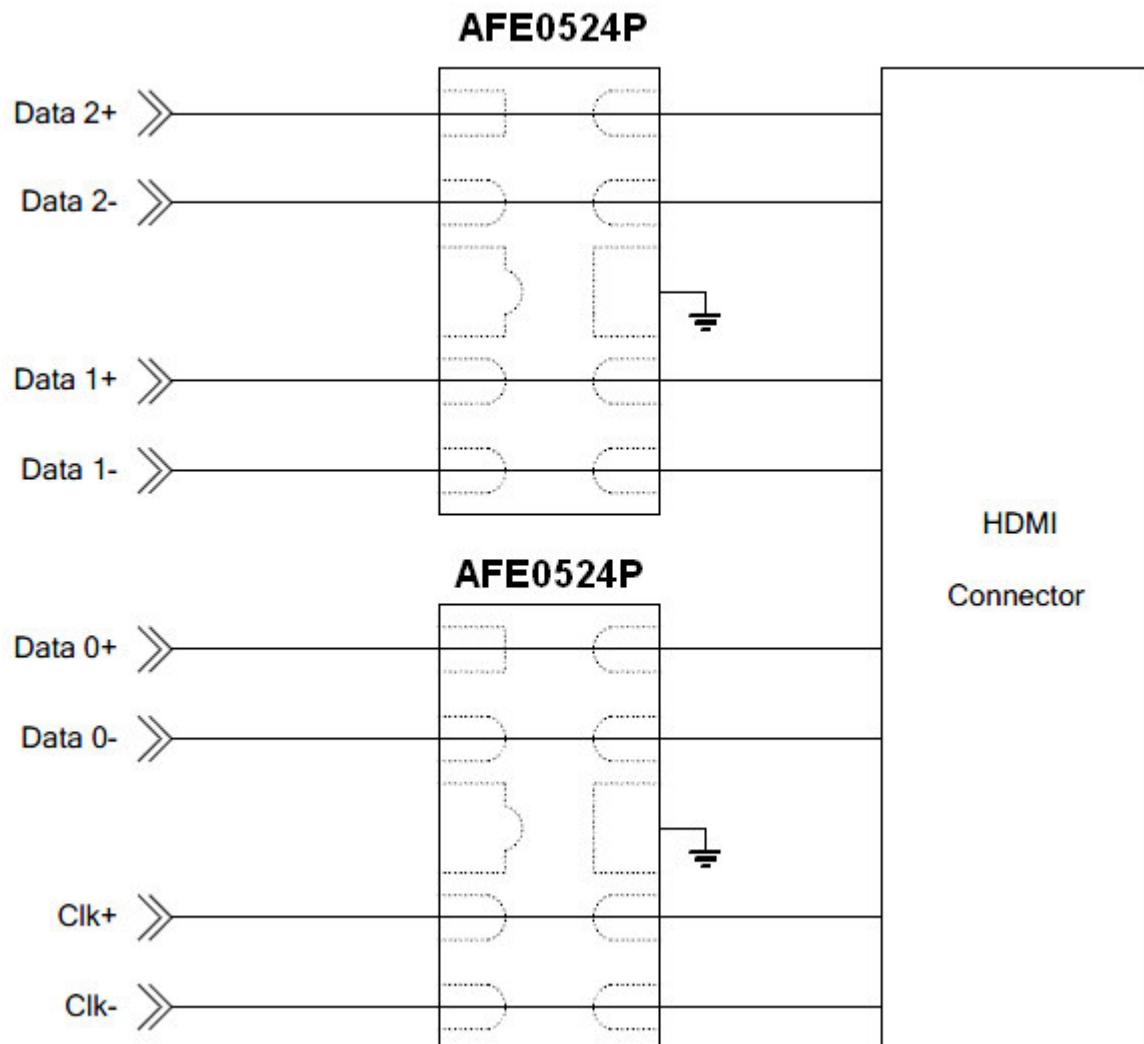




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**Application Information
(HDMI Port Application)**

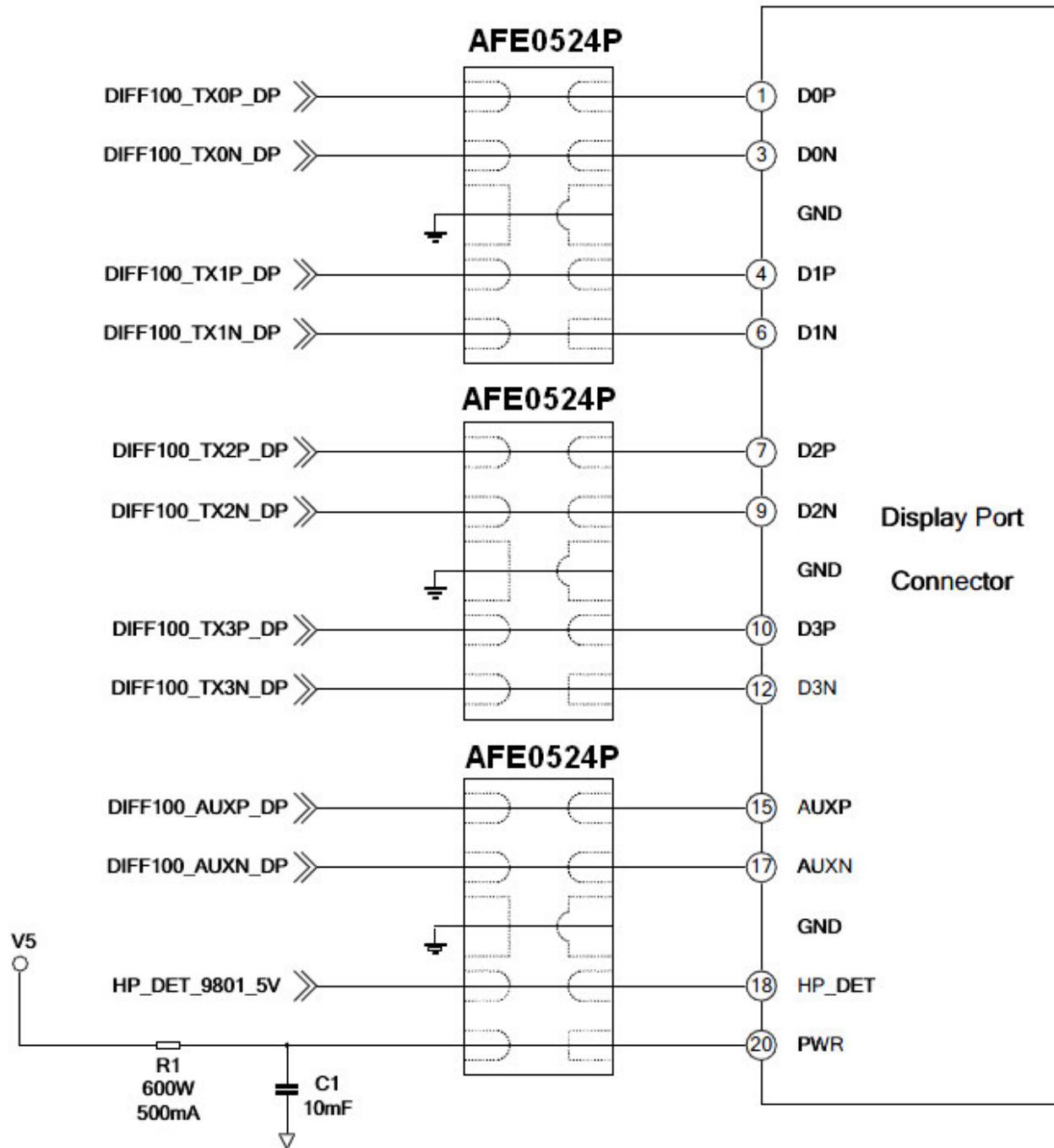




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**Application Information
(Display Port Application)**

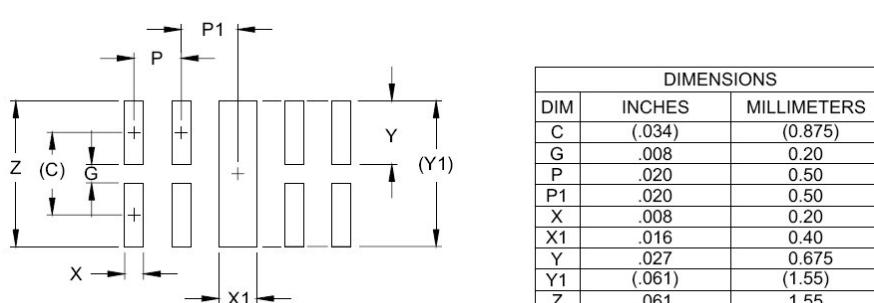
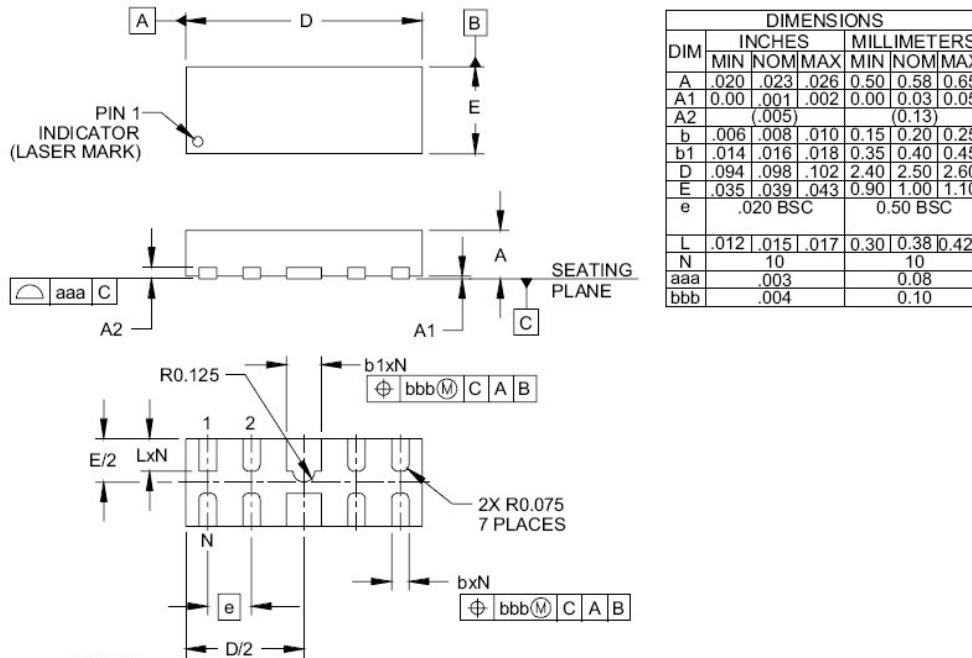




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Package Information (DFN-10)



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